Rectifier diodes schottky barrier

PBYR20100CTB series

GENERAL DESCRIPTION

Dual low leakage, platinum barrier, schottky rectifier diodes in a plastic envelope suitable for surface mounting, featuring low forward voltage drop, absence of stored charge. and guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

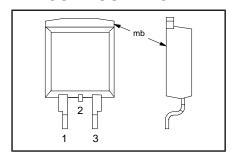
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{RRM}	PBYR20- Repetitive peak reverse voltage	60CTB 60	80CTB 80	100CTB 100	V
V _F I _{O(AV)}	Forward voltage Output current (both diodes conducting)	0.7 20	0.7 20	0.7 20	V A

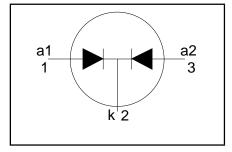
PINNING - SOT404

PIN	DESCRIPTION	
1	anode 1	
2	cathode	
3	anode 2	
mb	cathode	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{mb} ≤ 139 °C		- 60 60 60 60	-80 80 80 80	-100 100 100 100	V V
I _{O(AV)}	Output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 133 ^{\circ}\text{C}$	-		20		А
I _{O(RMS)}	RMS forward current	· mb = .00	-		28		A
I _{FRM}	Repetitive peak forward current per diode	$t = 25 \mu s$; $δ = 0.5$; $T_{mb} \le 133 °C$	-		20		Α
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-		135		Α
	current per diode.	t = 8.3 ms sinusoidal $T_i = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM}(\text{max})}$	-		150		A
l ² t	I ² t for fusing	t = 10 ms	-		91		A ² s
I _{RRM}	Repetitive peak reverse current per diode.		-		1		Α
I _{RSM}	Non-repetitive peak reverse current per diode.	$t_{p} = 100 \ \mu s$	-		1		Α
$\begin{bmatrix} T_{stg} \\ T_{j} \end{bmatrix}$	Storage temperature Operating junction temperature		-65 -		175 150		°C °C

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	per diode both diodes pcb mounted, minimum footprint	1 1 1	- - 50	2.0 1.0 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage (per diode)	I _F = 10 A; T _j = 125°C I _F = 20 A; T _j = 125°C	-	0.61	0.70	V
	- "	$I_{\rm F} = 20 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.74	0.85	V
		$I_{\rm F} = 20 \text{ A}, T_{\rm i} = 25 ^{\circ} \text{C}$	-	0.88	0.95	V
I _R	Reverse current (per diode)	$ V_R = V_{RRM}; T_i = 25 ^{\circ}C$	-	5.0	150	μΑ
''	i ,	$V_{R} = V_{RRM}^{(i)}; T_{j} = 125 ^{\circ}C$	-	5.0	15	mΑ
C _d	Junction capacitance (per diode)	$f = 1MHz$; $V_R = 5V$; $T_j = 25$ °C to 125 °C	-	420	-	pF

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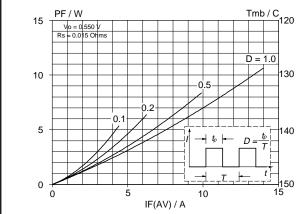


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

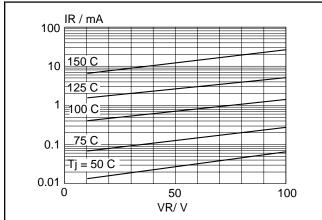


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

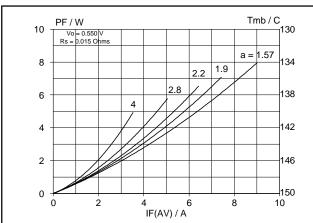


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f form factor $= I_{F(RMS)} / I_{F(AV)}$.

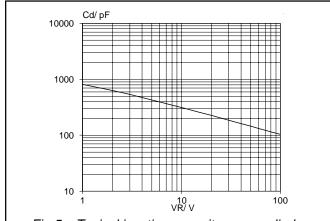


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

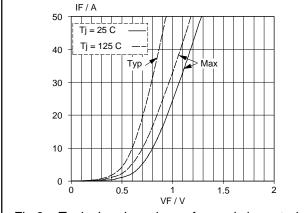


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

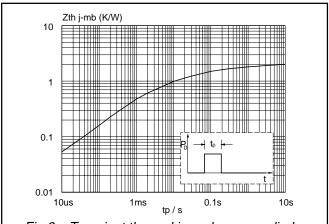
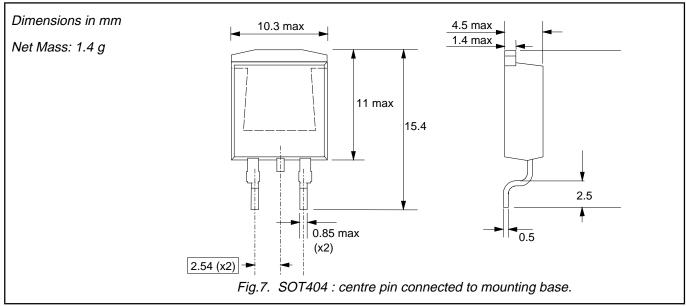


Fig.6. Transient thermal impedance per diode; $Z_{th j\text{-}mb} = f(t_p)$.

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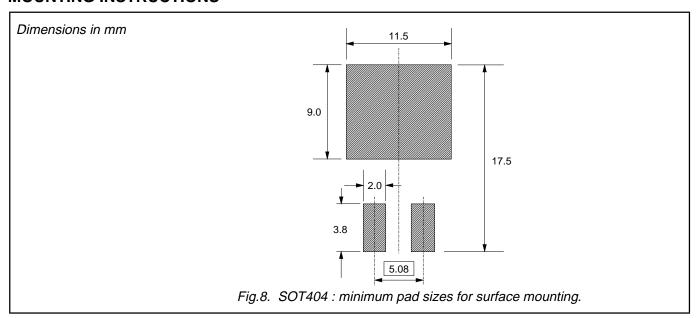
MECHANICAL DATA



Notes

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	Preliminary specification This data sheet contains preliminary data; supplementary data may be published late				
Product specification This data sheet contains final product specifications.					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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